NSN 5961-01-355-7547

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-355-7547 **Inclosure Material:** Metal **Overall Length:** Between 0.165 inches and 0.185 inches **Terminal Length:** Between 0.500 inches and 0.560 inches **Overall Diameter:** Between 0.340 inches and 0.370 inches **Component Name And Quantity:** 2 transistor **Mounting Method: Terminal Terminal Circle Diameter:** 0.200 inches **Features Provided:** Burn in **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 10.0 collector to base voltage, dc all transistor and 5.0 emitter to base, rms all transistor **Current Rating Per Characteristic:** 50.00 milliamperes source cutoff current all transistor **Power Rating Per Characteristic:** 200.0 milliwatts small-signal input power, common-collector preset all transistor **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius junction **Special Features:** All transistor junction pattern arrangement: npn **Terminal Type And Quantity:** 8 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** Fiig:

No

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